



### March 2004 Special Issue on Scaled Nano Devices

As an emerging technological importance for the next generation semiconductor fields, Journal of Semiconductor Technology and Science will publish the special issue of "Scaled Nano Devices". This special issue intends to disseminate the recent advances and their views on the future perspectives of research in the field of scaled nano devices including physics and devices, device structure and fabrication process, and measurements and characterization. The proposed topic areas will include but are not limited to the following:

#### 1. Physics and Devices

- Deep scaled MOSFET operation and performance
- Quantum effect devices and single electron devices
- Modeling and simulation
- Analog and RF devices for low voltage and high speed applications

#### 2. Device Structure and Fabrication Process

- Novel device structure
- Advance process integration for ULSI, memories, SOI, and system ICs
- Nano scale process modules
- Process control and process-induced damage

#### 3. Measurements and Characterization

- Electrical characterization technologies and parameter extraction
- Device and process related reliability issues

Authors wishing to have their contribution considered for publication in this Special Issue, which will be published in March 2004 issue, are invited to submit an electronic copy of their manuscripts to Editor Dr. Kyungho Lee ([khlee@won.hongik.ac.kr](mailto:khlee@won.hongik.ac.kr)), at no later than Dec. 31, 2003. Manuscripts should be submitted in free style double spaced MS word format as an email attachment. See <http://www.jsts.org> for detail. Both regular papers as well as letters are welcome.

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